

IGBT Discrete

V _{CE}	600	V
$I_{\rm C}$	30	A
V _{CE(SAT)} I _C =30A	1.5	V

Applications

- · Inverter for motor drive
- AC and DC servo drive amplifier
- Uninterruptible power supply

Features

- High breakdown voltage to 600V for improved reliability
- Maximum junction temperature 175℃
- · Positive temperature coefficient
- . Including fast & soft recovery anti-parallel FWD
- High short circuit capability(10us)

Maximum Ratings ($T_j = 25$ °C unless otherwise specified):

Parameter	Symbol	Value	Unit
Collector-Emitter Breakdown Voltage	V_{CE}	600	V
DC Collector Current, limited by T_{jmax} $T_C = 25$ °C $T_C = 100$ °C	I_{C}	60 30	A
Diode Forward Current, limited by T_{jmax} $T_C = 25$ °C $T_C = 100$ °C	${ m I}_{ m F}$	60 30	A
Continuous Gate-Emitter Voltage	V_{GE}	±20	V
Transient Gate-Emitter Voltage (tp≤10μs,D<0.010)	V_{GE}	±30	V
Pulsed Collector Current, V_{GE} =15V, tp limited by T_{jmax}	Ісм	90	A
Diode Pulsed Current, tp limited by T _{jmax}	I_{Fpuls}	90	A
Power Dissipation ,Tc=25°C	P _{tot}	195	W
Power Dissipation, Tc=100°C	P _{tot}	81	W

Rev.1.0



Operating Junction Temperature	T _j	-40+175	°C
Storage Temperature	T_s	-55+150	°C
Soldering Temperature, wave soldering 1.6mm (0.063in.) from case for 10s		260	°C

Electrical Characteristics of the IGBT $(T_j=25^{\circ}Cunless otherwise specified)$:

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Static						
Collector-Emitter Breakdown Voltage	BV _{CES}	V _{GE} =0V, I _C =250μA	600	697	-	V
Gate Threshold Voltage	V _{GE(th)}	$V_{GE}=V_{CE}, I_{C}=1 \text{ mA}$	4	6.33	7.5	V
Collector-Emitter Saturation Voltage	V _{CE(sat)}	$V_{GE}=15V, I_{C}=30A$ $T_{j}=25^{\circ}C,$ $T_{j}=125^{\circ}C$ $T_{j}=150^{\circ}C$		1.6 1.8 2.0	2.0	V
Zero Gate Voltage Collector Current	I _{CES}	V _{CE} =600V, V _{GE} =0V T _j = 25°C, T _j =150°C			8.06 10.9	nA
Gate-Emitter Leakage Current	I _{GES}	V_{CE} = 0V, V_{GE} = ± 20V			±250	nA

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Dynamic						
Input Capacitance	Cies		ı	1450	-	
Onput Capacitance	Coes	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz	-	75	-	pF
Reverse Transfer Capacitance	Cres		-	27	-	
Gate Charge	Qg		-	134	-	
Gate-Emitter Charge	Q_{ge}	V _{CC} =300V,I _C =30A, V _{GE} =15V	-	31	-	nC
Gate-Collector Charge	$Q_{ m gc}$		-	69	-	



Switching Characteristic, Inductive Load (T_j= 25 °C unless otherwise specified):

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-on Delay Time	t _{d(on)}		-	22	-	ns
Rise Time	$t_{\rm r}$		-	31	-	ns
Turn-on Energy	Eon	V_{CC} = 300V, I_{C} =20A, V_{GE} = -15V~15V,	-	0.8	-	mJ
Turn-off Delay Time	$t_{d(off)}$	$R_g=10\Omega$	-	152	-	ns
Fall Time	t_{f}		-	20	-	ns
Turn-off Energy	E _{off}		-	0.4	-	mJ

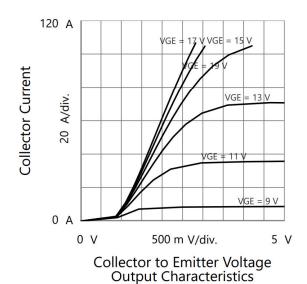
Electrical Characteristics of the DIODE $(T_j=25^{\circ}Cunless otherwise specified)$:

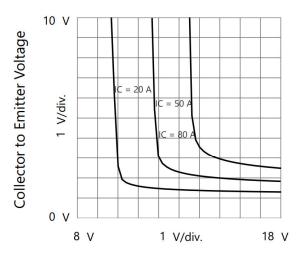
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Diode Forward Voltage	V_{F}	$I_F=20A$	-	1.5	1.9	V
Reverse Recovery Current	I_{rr}		-	4	-	A
Reverse Recovery Charge	Qrr	I_F =20A, V_R =300V, di/dt= -200A/ μ s,	-	405	-	nC
Reverse Recovery Energy	Erec		-	0.15		mJ

Thermal Resistance

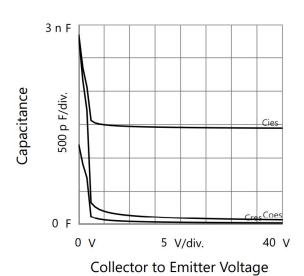
Parameter	Symbol	Max. Value	Unit
IGBT Thermal Resistance, Junction - Case	R _{th} (j-c)	0.65	K/W
Diode Thermal Resistance, Junction - Case	R _{th} (j-c)	1.09	K/W
Thermal Resistance, Junction - Ambient	R _{th} (j-a)	40	K/W



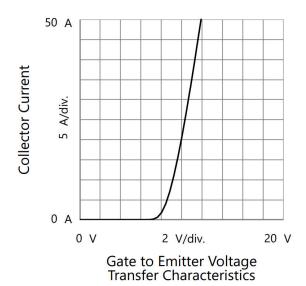


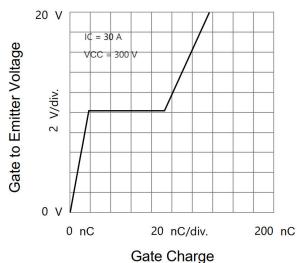


Gate to Emitter Voltage
Collector to Emitter Voltage vs. Gate to Emitter Voltage
Capacitances

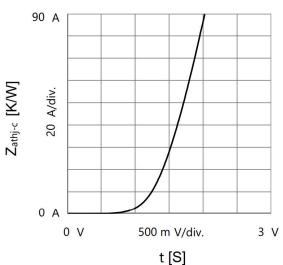


Capacitances

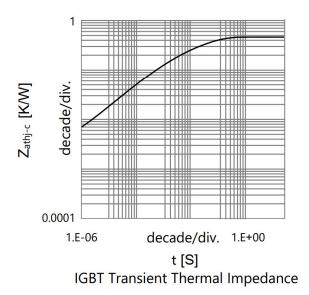


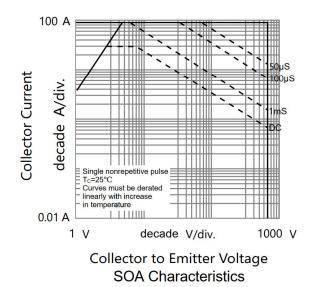


Gate to Emitter Voltage vs. Gate Charge



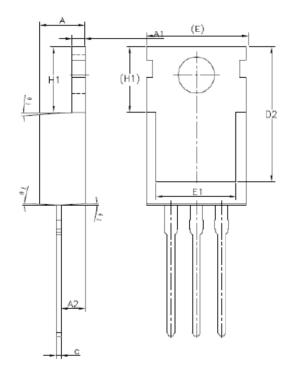
IGBT Transient Thermal Impedance

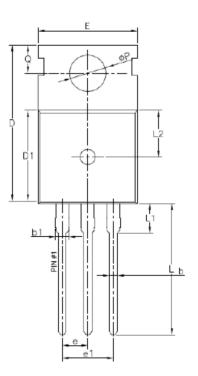




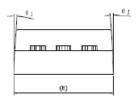


TO-220 Package Outline Information





SYMBOL	MIN	NOM	MAX
A	4.40	4.50	4.60
A1	1.27	1.30	1.33
A2	2.30	2.40	2.50
b	0.70	-	0.90
b1	1.27	-	1.40
С	0.45	0.50	0.60
D	15.30	15.70	16.10
D1	9.10	9.20	9.30
D2	13.10	_	13.70
Ε	9.70	9.90	10.20
E1	7.80	8.00	8.20
е	2.49	2.54	2.59
e1	5.03	5.08	5.12
H1	6.30	6.50	6.70
L	12.78	13.08	13.38
L1	3.30	_	3.50
L2	4.50	4.60	4.70
ØΡ	3.55	3.60	3.65
Q	2.73	_	2.87
θ 1	1"	3°	5"



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